L Number	Hits	Search Text	DB	Time stamp
101	0		USPAT;	2004/08/18 13:39
		. , , , , , , , , , , , , , , , , , , ,	EPO; JPO;	2001,00,10 15:55
			DERWENT;	
1			IBM_TDB	
102	1	wafer same photoexcitation same wavelength	USPAT;	2004/08/18 13:40
	İ		EPO; JPO;	
İ			DERWENT;	
103	84	wafer and photographetics and annual and	IBM_TDB	0004/00/40 45 55
103	F 0	wafer and photoexcitation and wavelength	USPAT;	2004/08/18 15:05
			EPO; JPO; DERWENT;	
			IBM TDB	
104	121	wafer and electromotive and wavelength	USPAT;	2004/08/18 15:04
			EPO; JPO;	=====================================
			DERWENT;	
105	101		IBM_TDB	
105	121	wafer and photoexcitation	USPAT;	2004/08/18 14:13
			EPO; JPO;	,
			DERWENT;	
106	489	substrate and electromotive and wavelength	IBM_TDB USPAT;	2004/09/10 15-05
	1	substitute and electionocive and wavelength	EPO; JPO;	2004/08/18 15:05
			DERWENT;	
			IBM TDB	
107	120	substrate and photoexcitation and	USPAT;	2004/08/18 15:05
		wavelength and clean\$4	EPO; JPO;	
	ļ		DERWENT;	
108	750	substrate some (leave and during)	IBM_TDB	
100	/30	substrate same (laser or irradiated or irradiating) same clean\$4 same (UV or	USPAT;	2004/08/18 15:11
		ultraviolet or wavelength)	EPO; JPO; DERWENT;	1
		alterationed of wavelength)	IBM TDB	
109	12	substrate same (laser or irradiated or	USPAT;	2004/08/18 15:10
-		irradiating) same clean\$4 same (UV or	EPO; JPO;	2004/00/10 15:10
		ultraviolet or wavelength) same wiring	DERWENT;	
110		_	IBM TDB	
110	290		USPAT;	2004/08/18 15:25
	•	irradiating) same clean\$4 same wavelength	EPO; JPO;	
			DERWENT;	
111	105	wafer same (laser or irradiated or	IBM_TDB USPAT;	2004/00/10 15 24
		irradiating) same clean\$4 same wavelength	EPO; JPO;	2004/08/18 15:34
		and the state of t	DERWENT;	
			IBM TDB	ļ
112	695	, and the transfer of fitalitated	USPAT;	2004/08/18 15:36
		or irradiating) and clean\$4 and	EPO; JPO;	
		wavelength	DERWENT;	l
113	184	wafor and wining and /lease as to live a	IBM_TDB	
113	104	wafer and wiring and (laser or irradiated or irradiating) and clean\$4 and "500 nm"	USPAT;	2004/08/18 15:56
		or remarkating, and creamys and 500 nm"	EPO; JPO; DERWENT;	
			IBM TDB	
114	1		USPAT	2004/08/18 15:39
115	695	wafer and wiring and (laser or irradiated	USPAT;	2004/08/18 15:57
		or irradiating) and clean\$4 and wavelength	EPO; JPO;	
			DERWENT;	
116	40	wafor and wining and the	IBM_TDB	
110	40	wafer and wiring and (laser or irradiated or irradiating) and clean\$4 and wavelength	USPAT;	2004/08/18 16:05
		and "PN junction"	EPO; JPO; DERWENT;	
			IBM TDB	
117	695	wafer and wiring and (laser or irradiated	USPAT;	2004/08/18 16:06
		or irradiating) and clean\$4 and wavelength	EPO; JPO;	2001/00/10 10:00
	ļ	. 3	DERWENT;	
110	[IBM_TDB	
118	69	wafer and wiring and (laser or irradiated	USPĀT;	2004/08/18 16:06
	ł	or irradiating) and clean\$4 and wavelength	EPO; JPO;	
		and CMP	DERWENT;	
119	1		IBM_TDB USPAT	2004/09/10 10 00
			OPENI	2004/08/18 16:06